

General Description

The WSF3095G is the highest performance SGT N-Channel MOSFET with extreme high cell density, which provide excellent $R_{DS(ON)}$ and gate charge for most of the synchronous buck converter applications.

The WSF3095G meet the RoHS and Green Product requirement, 100% E_{AS} guaranteed with full function reliability approved.

Features

- 100% UIS + R_g Tested.
- Reliable and Rugged
- Lead Free and Green Devices Available (RoHS Compliant)

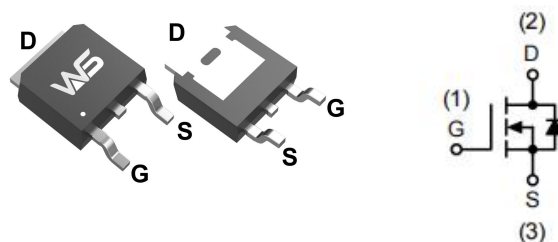
Product Summary

BV_{DSS}	$R_{DS(ON)}$	I_D
30V	4.0m Ω	90A

Applications

- Power Management for Industrial DC/DC Converters
- Ideal for high-frequency switching and synchronous rectification

TO-252-2L Pin Configuration



Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$, Unless Otherwise Noted)

Symbol	Parameter		Rating	Units
V_{DS}	Drain-Source Voltage		30	V
V_{GS}	Gate-Source Voltage		± 20	
I_D ⁷	Continuous Drain Current	$T_C=25^{\circ}\text{C}$	90	A
		$T_C=100^{\circ}\text{C}$	45	
I_{DM} ³	Pulse Drain Current		146	
P_D ²	Power Dissipation	$T_C=25^{\circ}\text{C}$	28	W
I_{AS} ³	Single pulse Avalanche Current		27	A
E_{AS} ³	Single pulse Avalanche Energy	$L=0.5\text{mH}$	36	mJ
T_{STG}	Storage Temperature Range		-55 to 150	$^{\circ}\text{C}$
T_J	Operating Junction Temperature Range		-55 to 150	
$R_{\theta JA}$ ^{1,4}	Thermal Resistance-Junction to Ambient	$t \leq 10\text{s}$	31	$^{\circ}\text{C/W}$
		Steady State	62.5	
$R_{\theta JC}$	Thermal Resistance-Junction to Case		0.83	

Electrical Characteristics ($T_J=25^{\circ}\text{C}$, Unless Otherwise Noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	30	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10V$, $I_D=10A$	---	4.0	4.8	m Ω
		$T_J=125^{\circ}\text{C}$	---	8.0	9.6	
		$V_{GS}=4.5V$, $I_D=5A$	---	5.3	6.6	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	1.0	1.6	2.5	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=30V$, $V_{GS}=0V$	---	---	1.0	μA
		$T_J=55^{\circ}\text{C}$	---	---	5.0	
I_{GSS}	Gate-Source Leakage Current	$V_{DS}=0V$, $V_{GS}=\pm 10V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=5V$, $I_D=20A$	---	30	---	S
R_G	Gate Resistance	$f=1.0\text{MHz}$	1.0	2.0	3.1	Ω
Q_g	Total Gate Charge (10V)	$V_{DS}=15V$, $V_{GS}=10V$, $I_D=4.5A$	---	13.8	---	nC
Q_{gs}	Gate-Source Charge		---	2.7	---	
Q_{gd}	Gate-Drain Charge		---	3.0	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DS}=15V$, $V_{GS}=4.5V$, $R_L=1\Omega$, $R_{GEN}=3\Omega$	---	6.5	---	ns
T_r	Rise Time		---	2.5	---	
$T_{d(off)}$	Turn-Off Delay Time		---	17	---	
T_f	Fall Time		---	2.5	---	
C_{iss}	Input Capacitance	$V_{DS}=15V$, $V_{GS}=0V$, $f=1.0\text{MHz}$	---	812	---	pF
C_{oss}	Output Capacitance		---	344	---	
C_{rss}	Reverse Transfer Capacitance		---	15.3	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
I_S ⁷	Continuous Source Current		---	---	45	A
V_{SD}	Diode Forward Voltage	$V_{GS}=0V$, $I_S=1A$	---	---	1.4	V
t_{rr}	Reverse Recovery Time	$I_F=20A$, $di/dt=500A/\mu s$	---	11	---	ns
Q_{rr}	Reverse Recovery Charge		---	19	---	nC

Note:

- The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^{\circ}\text{C}$. The Power dissipation P_{DSM} is based on $R_{\theta JA} \leq 10s$ and the maximum allowed junction temperature of 150°C . The value in any given application depends on the user's specific board design.
- The power dissipation P_D is based on $T_{J(MAX)}=150^{\circ}\text{C}$, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
- Single pulse width limited by junction temperature $T_{J(MAX)}=150^{\circ}\text{C}$.
- The $R_{\theta JA}$ is the sum of the thermal impedance from junction to case $R_{\theta JC}$ and case to ambient.
- The static characteristics in Figures 1 to 6 are obtained using $<300\mu s$ pulses, duty cycle 0.5% max.
- These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}=150^{\circ}\text{C}$. The SOA curve provides a single pulse rating.
- The maximum current rating is package limited.
- These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^{\circ}\text{C}$.
- The maximum current rating is silicon limited

Typical Characteristics

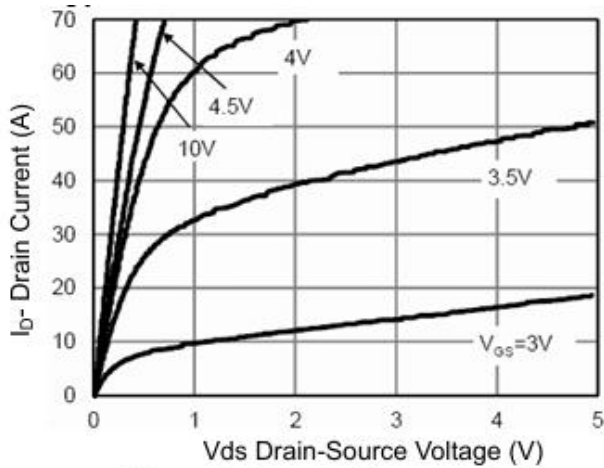


Figure 1 Output Characteristics

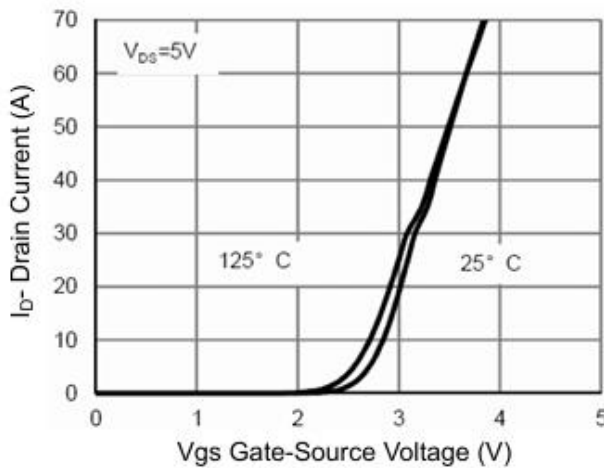


Figure 2 Transfer Characteristics

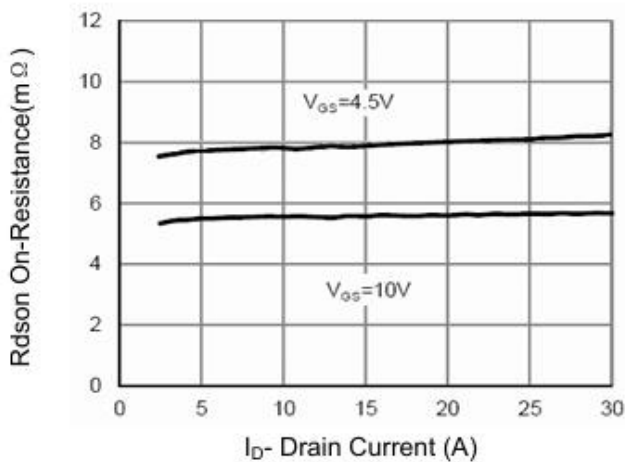


Figure 3 Rdson- Drain Current

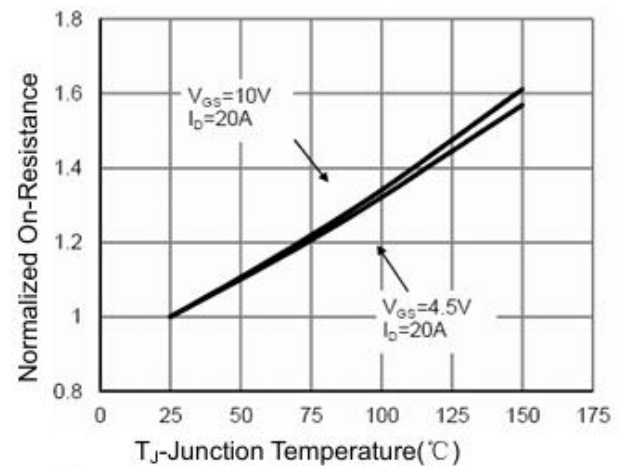


Figure 4 Rdson-Junction Temperature

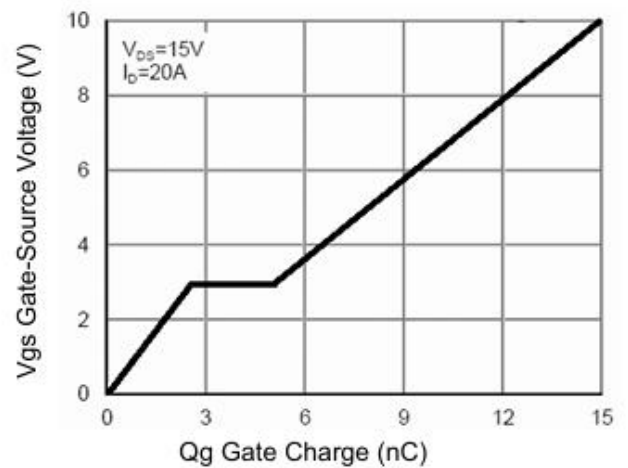


Figure 5 Gate Charge

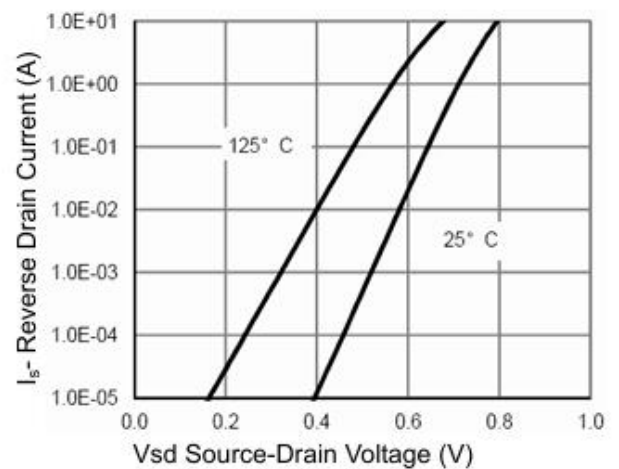


Figure 6 Source- Drain Diode Forward

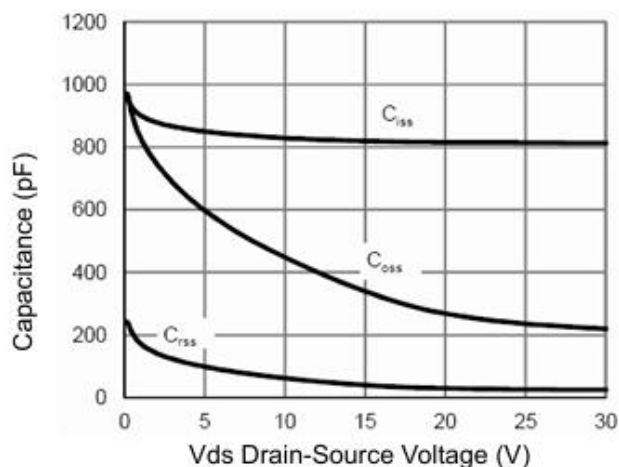


Figure 7 Capacitance vs Vds

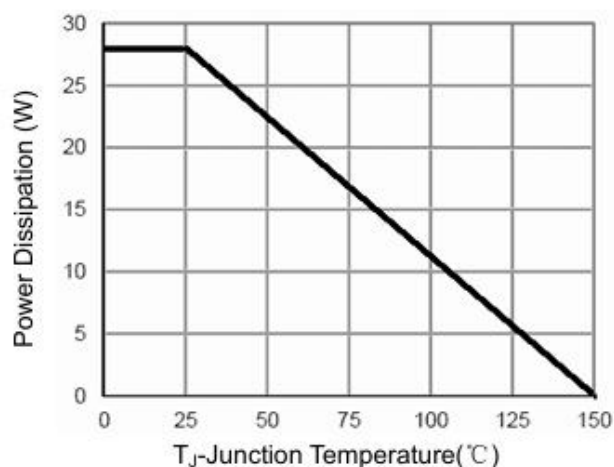


Figure 9 Power De-rating

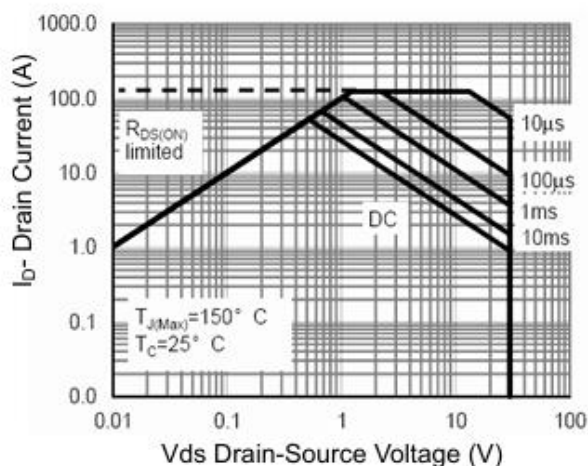


Figure 8 Safe Operation Area

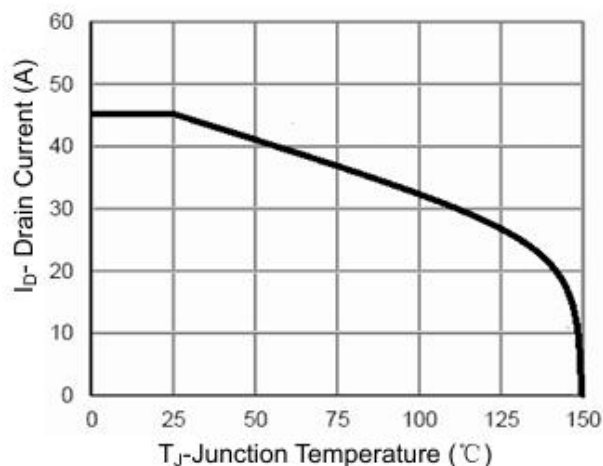


Figure 10 Current De-rating

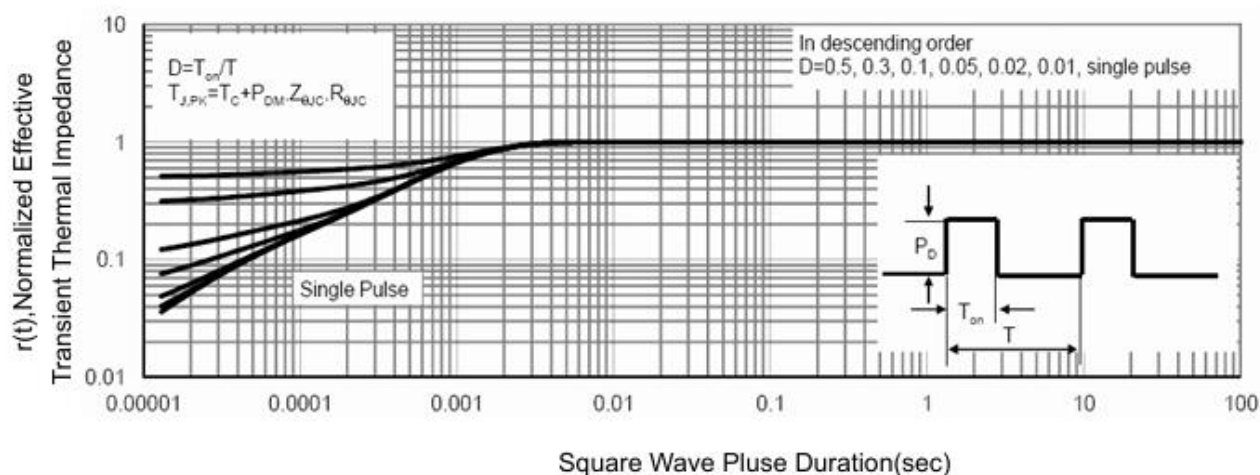
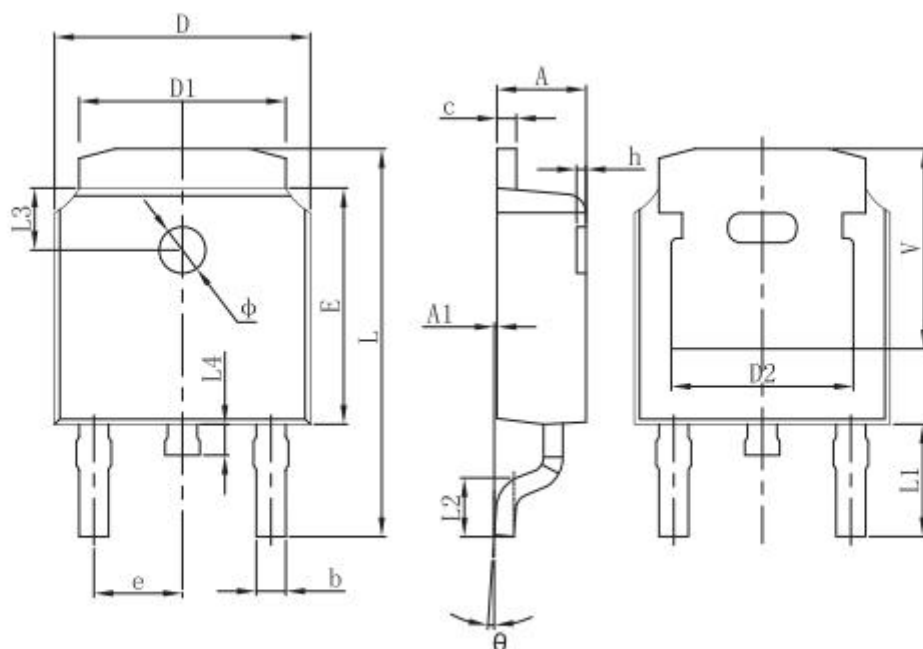


Figure 11 Normalized Maximum Transient Thermal Impedance

Packaging information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.635	0.770	0.025	0.030
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.712	10.312	0.382	0.406
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	1.600 REF.		0.063 REF.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.250 REF.		0.207 REF.	

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